

Document Title

**512Kx8 Bit High Speed Static RAM(5V Operating).
Operated at Extended and Industrial Temperature Ranges.**

Revision History

<u>RevNo.</u>	<u>History</u>	<u>Draft Data</u>	<u>Remark</u>																													
Rev. 0.0	Initial release with Preliminary.	Feb. 12. 1999	Preliminary																													
Rev. 1.0	1.1 Removed Low power Version. 1.2 Removed Data Retention Characteristics. 1.3 Changed I _{SB1} to 20mA	Mar. 29. 1999	Preliminary																													
Rev. 2.0	2.1 Relax D.C parameters.	Aug. 19. 1999	Preliminary																													
<table><tr><th colspan="2">Item</th><th>Previous</th><th>Current</th></tr><tr><td rowspan="3">I_{cc}</td><td>12ns</td><td>170mA</td><td>195mA</td></tr><tr><td>15ns</td><td>165mA</td><td>190mA</td></tr><tr><td>20ns</td><td>160mA</td><td>185mA</td></tr></table>				Item		Previous	Current	I _{cc}	12ns	170mA	195mA	15ns	165mA	190mA	20ns	160mA	185mA															
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I _{cc}	12ns	170mA	195mA																													
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	20ns	160mA	185mA																													
2.2 Relax Absolute Maximum Rating.																																
<table><tr><th>Item</th><th>Previous</th><th>Current</th></tr><tr><td>Voltage on Any Pin Relative to V_{SS}</td><td>-0.5 to 7.0</td><td>-0.5 to V_{CC}+0.5</td></tr></table>				Item	Previous	Current	Voltage on Any Pin Relative to V _{SS}	-0.5 to 7.0	-0.5 to V _{CC} +0.5																							
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Rev. 3.0	3.1 Delete Preliminary 3.2 Update D.C parameters and 10ns part.	Mar. 27. 2000	Final																													
<table><tr><th rowspan="2"></th><th colspan="3">Previous</th><th colspan="3">Current</th></tr><tr><th>I_{cc}</th><th>I_{sb}</th><th>I_{sb1}</th><th>I_{cc}</th><th>I_{sb}</th><th>I_{sb1}</th></tr><tr><td>10ns</td><td>-</td><td rowspan="4">70mA</td><td rowspan="4">20mA</td><td>170mA</td><td rowspan="4">60mA</td><td rowspan="4">10mA</td></tr><tr><td>12ns</td><td>195mA</td><td>160mA</td></tr><tr><td>15ns</td><td>190mA</td><td>150mA</td></tr><tr><td>20ns</td><td>185mA</td><td>140mA</td></tr></table>					Previous			Current			I _{cc}	I _{sb}	I _{sb1}	I _{cc}	I _{sb}	I _{sb1}	10ns	-	70mA	20mA	170mA	60mA	10mA	12ns	195mA	160mA	15ns	190mA	150mA	20ns	185mA	140mA
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3.3 Added Extended temperature range																																

The attached data sheets are prepared and approved by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications. SAMSUNG Electronics will evaluate and reply to your requests and questions on the parameters of this device. If you have any questions, please contact the SAMSUNG branch office near your office, call or contact Headquarters.

512K x 8 Bit High-Speed CMOS Static RAM

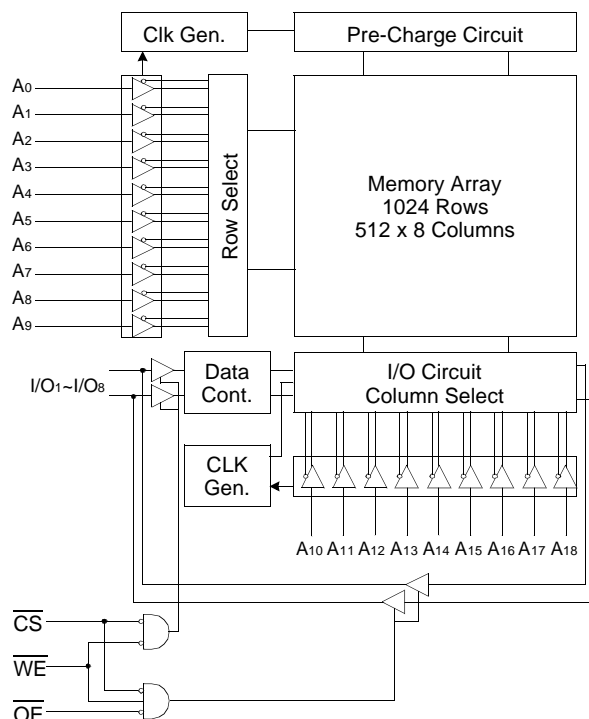
FEATURES

- Fast Access Time 10,12,15,20ns(Max.)
- Low Power Dissipation
 - Standby (TTL) : 60mA(Max.)
 - (CMOS) : 10mA(Max.)
 - Operating KM684002C-10 : 170mA(Max.)
 - KM684002C-12 : 160mA(Max.)
 - KM684002C-15 : 150mA(Max.)
 - KM684002C-20 : 140mA(Max.)
- Single 5.0V±10% Power Supply
- TTL Compatible Inputs and Outputs
- I/O Compatible with 3.3V Device
- Fully Static Operation
 - No Clock or Refresh required
- Three State Outputs
- Center Power/Ground Pin Configuration
- Standard Pin Configuration
 - KM684002CJ : 36-SOJ-400
 - KM684002CT : 44-TSOP2-400BF

GENERAL DESCRIPTION

The KM684002C is a 4,194,304-bit high-speed Static Random Access Memory organized as 524,288 words by 8 bits. The KM684002C uses 8 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. The device is fabricated using SAMSUNG's advanced CMOS process and designed for high-speed circuit technology. It is particularly well suited for use in high-density high-speed system applications. The KM684002C is packaged in a 400 mil 36-pin plastic SOJ and 44-pin plastic TSOP type II.

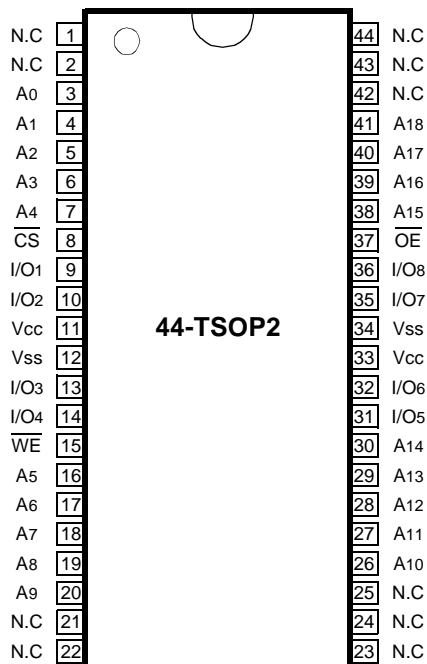
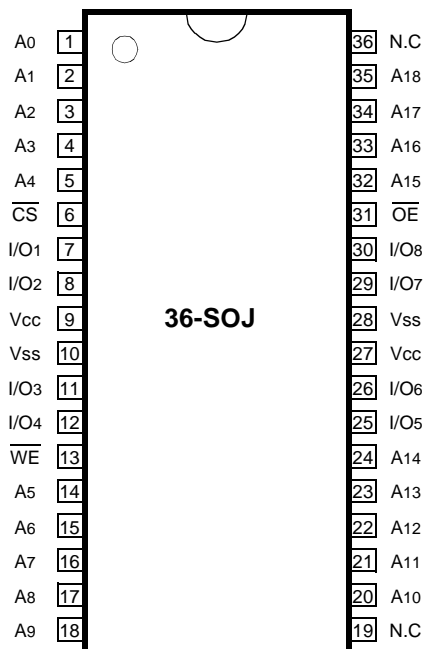
FUNCTIONAL BLOCK DIAGRAM



ORDERING INFORMATION

KM684002C-10/12/15/20	Commercial Temp.
KM684002C-10/12/15/20	Extended Temp.
KM684002C-10/12/15/20	Industrial Temp.

PIN CONFIGURATION (Top View)



PIN FUNCTION

Pin Name	Pin Function
A0 - A18	Address Inputs
$\overline{\text{WE}}$	Write Enable
$\overline{\text{CS}}$	Chip Select
$\overline{\text{OE}}$	Output Enable
I/O1 ~ I/O8	Data Inputs/Outputs
Vcc	Power(+5.0V)
Vss	Ground
N.C	No Connection

ABSOLUTE MAXIMUM RATINGS*

Parameter		Symbol	Rating	Unit
Voltage on Any Pin Relative to Vss		V _{IN} , V _{OUT}	-0.5 to Vcc+0.5	V
Voltage on Vcc Supply Relative to Vss		Vcc	-0.5 to 7.0	V
Power Dissipation		P _D	1.0	W
Storage Temperature		T _{STG}	-65 to 150	°C
Operating Temperature	Commercial	T _A	0 to 70	°C
	Extended	T _A	-25 to 85	°C
	Industrial	T _A	-40 to 85	°C

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS*($T_A=0$ to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Ground	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.2	-	$V_{CC}+0.5^{***}$	V
Input Low Voltage	V_{IL}	-0.5**	-	0.8	V

* The above parameters are also guaranteed at extended and industrial temperature range.

** $V_{IL}(\text{Min}) = -2.0\text{V}$ a.c(Pulse Width $\leq 8\text{ns}$) for $I \leq 20\text{mA}$.

*** $V_{IH}(\text{Max}) = V_{CC} + 2.0\text{V}$ a.c (Pulse Width $\leq 8\text{ns}$) for $I \leq 20\text{mA}$.

DC AND OPERATING CHARACTERISTICS*($T_A=0$ to 70°C , $V_{CC}=5.0\text{V} \pm 10\%$, unless otherwise specified)

Parameter	Symbol	Test Conditions			Min	Max	Unit
Input Leakage Current	I _{LI}	V _{IN} =V _{SS} to V _{CC}			-2	2	μA
Output Leakage Current	I _{LO}	CS=V _{IH} or OE=V _{IH} or WE=V _{IL} V _{OUT} =V _{SS} to V _{CC}			-2	2	μA
Operating Current	I _{CC}	Min. Cycle, 100% Duty CS=V _{IL} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA	Com.	10ns	-	170	mA
				12ns	-	160	
				15ns	-	150	
				20ns	-	140	
		Ext. Ind.	10ns	-	185		
			12ns	-	175		
			15ns	-	165		
			20ns	-	155		
Standby Current	I _{SB}	Min. Cycle, CS=V _{IH}			-	60	mA
	I _{SB1}	f=0MHz, CS≥V _{CC} -0.2V, V _{IN} ≥V _{CC} -0.2V or V _{IN} ≤0.2V			-	10	mA
Output Low Voltage Level	V _{OL}	I _{OL} =8mA			-	0.4	V
Output High Voltage Level	V _{OH}	I _{OH} =-4mA			2.4	-	V
	V _{OH1} **	I _{OH1} =-0.1mA			-	3.95	V

* The above parameters are also guaranteed at extended and industrial temperature range.

** $V_{CC}=5.0\text{V} \pm 5\%$, Temp. $=25^{\circ}\text{C}$.

CAPACITANCE*($T_A=25^{\circ}\text{C}$, $f=1.0\text{MHz}$)

Item	Symbol	Test Conditions	MIN	Max	Unit
Input/Output Capacitance	$C_{I/O}$	$V_{I/O}=0\text{V}$	-	8	pF
Input Capacitance	C_{IN}	$V_{IN}=0\text{V}$	-	7	pF

* Capacitance is sampled and not 100% tested.

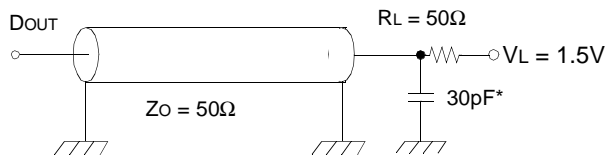
AC CHARACTERISTICS (T_A=0 to 70°C, V_{CC}=5.0V±10%, unless otherwise noted.)

TEST CONDITIONS*

Parameter	Value
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3ns
Input and Output timing Reference Levels	1.5V
Output Loads	See below

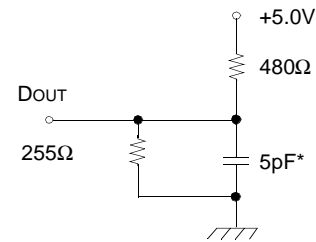
* The above test conditions are also applied at extended and industrial temperature range.

Output Loads(A)



Output Loads(B)

for t_{HZ}, t_{LZ}, t_{WHZ}, t_{OW}, t_{OLZ} & t_{OHZ}



* Capacitive Load consists of all components of the test environment.

* Including Scope and Jig Capacitance

READ CYCLE*

Parameter	Symbol	KM684002C-10		KM684002C-12		KM684002C-15		KM684002C-20		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	10	-	12	-	15	-	20	-	ns
Address Access Time	t _{AA}	-	10	-	12	-	15	-	20	ns
Chip Select to Output	t _{CO}	-	10	-	12	-	15	-	20	ns
Output Enable to Valid Output	t _{OE}	-	5	-	6	-	7	-	9	ns
Chip Enable to Low-Z Output	t _{LZ}	3	-	3	-	3	-	3	-	ns
Output Enable to Low-Z Output	t _{OLZ}	0	-	0	-	0	-	0	-	ns
Chip Disable to High-Z Output	t _{HZ}	0	5	0	6	0	7	0	9	ns
Output Disable to High-Z Output	t _{OHZ}	0	5	0	6	0	7	0	9	ns
Output Hold from Address	t _{OH}	3	-	3	-	3	-	3	-	ns
Chip Selection to Power Up Time	t _{PU}	0	-	0	-	0	-	0	-	ns
Chip Selection to Power Down-	t _{PD}	-	10	-	12	-	15	-	20	ns

* The above parameters are also guaranteed at extended and industrial temperature range.

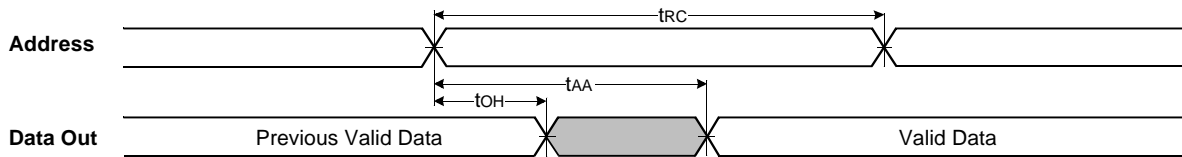
WRITE CYCLE*

Parameter	Symbol	KM684002C-10		KM684002C-12		KM684002C-15		KM684002C-20		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	tWC	10	-	12	-	15	-	20	-	ns
Chip Select to End of Write	tCW	7	-	8	-	10	-	12	-	ns
Address Set-up Time	tAS	0	-	0	-	0	-	0	-	ns
Address Valid to End of	tAW	7	-	8	-	10	-	12	-	ns
Write Pulse Width(\overline{OE} High)	tWP	7	-	8	-	10	-	12	-	ns
Write Pulse Width(\overline{OE} Low)	tWP1	10	-	12	-	15	-	20	-	ns
Write Recovery Time	tWR	0	-	0	-	0	-	0	-	ns
Write to Output High-Z	tWHZ	0	6	0	6	0	7	0	9	ns
Data to Write Time Overlap	tDW	5	-	6	-	7	-	9	-	ns
Data Hold from Write Time	tDH	0	-	0	-	0	-	0	-	ns
End Write to Output Low-Z	tOW	3	-	3	-	3	-	3	-	ns

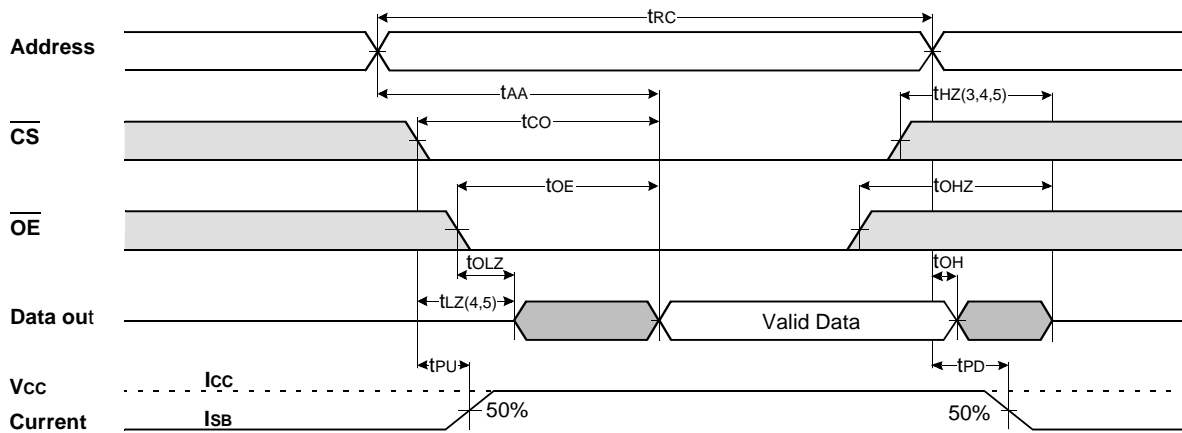
* The above parameters are also guaranteed at extended and industrial temperature range.

TIMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS}=\overline{OE}=V_{IL}$, $\overline{WE}=V_{IH}$)



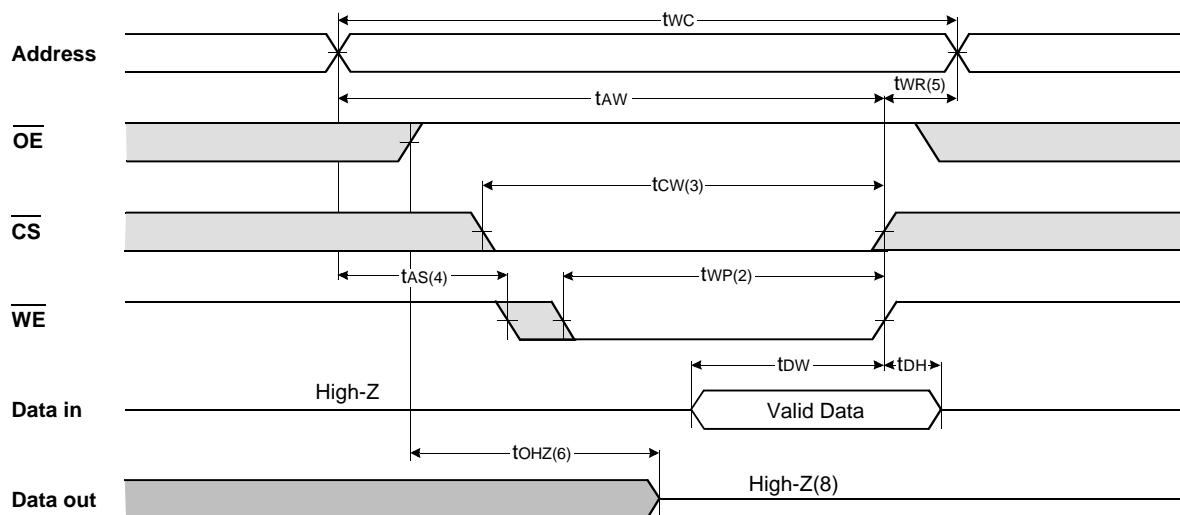
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)



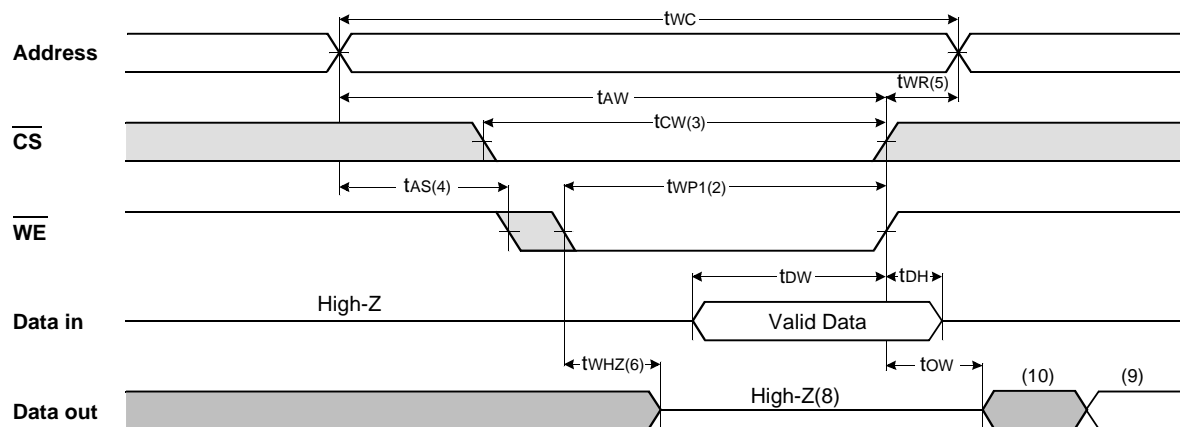
NOTES(WRITE CYCLE)

- \overline{WE} is high for read cycle.
- All read cycle timing is referenced from the last valid address to the first transition address.
- tHZ and tOHZ are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
- At any given temperature and voltage condition, tHZ(Max.) is less than tLZ(Min.) both for a given device and from device to device.
- Transition is measured $\pm 200mV$ from steady state voltage with Load(B). This parameter is sampled and not 100% tested.
- Device is continuously selected with $\overline{CS}=V_{IL}$.
- Address valid prior to coincident with \overline{CS} transition low.
- For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.

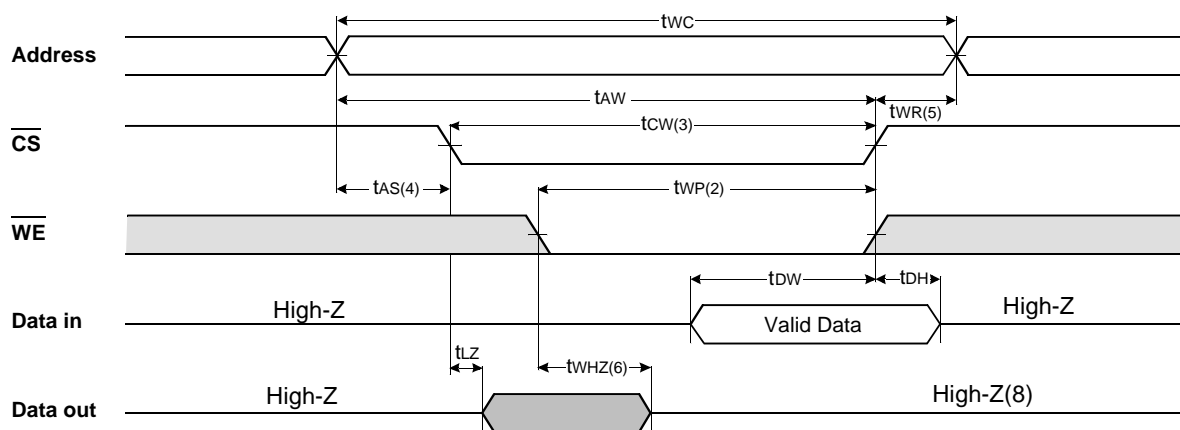
TIMING WAVEFORM OF WRITE CYCLE(1) (\overline{OE} = Clock)



TIMING WAVEFORM OF WRITE CYCLE(2) (\overline{OE} = Low Fixed)



TIMING WAVEFORM OF WRITE CYCLE(3) (\overline{CS} = Controlled)



NOTES(WRITE CYCLE)

1. All write cycle timing is referenced from the last valid address to the first transition address. \overline{CS} going low and \overline{WE} going low ; A write ends at the earliest transition \overline{CS} going high or \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
2. A write occurs during the overlap of a low \overline{CS} and \overline{WE} . A write begins at the latest transition \overline{CS} going low and \overline{WE} going low ; A write ends at the earliest transition \overline{CS} going high or \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
3. t_{CW} is measured from the later of \overline{CS} going low to end of write.
4. t_{AS} is measured from the address valid to the beginning of write.
5. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as \overline{CS} or \overline{WE} going high.
6. If \overline{OE} , \overline{CS} and \overline{WE} are in the Read Mode during this period, the I/O pins are in the output low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
7. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
8. If \overline{CS} goes low simultaneously with \overline{WE} going or after \overline{WE} going low, the outputs remain high impedance state.
9. DOUT is the read data of the new address.
10. When \overline{CS} is low : I/O pins are in the output state. The input signals in the opposite phase leading to the output should not be applied.

FUNCTIONAL DESCRIPTION

\overline{CS}	\overline{WE}	\overline{OE}	Mode	I/O Pin	Supply Current
H	X	X*	Not Select	High-Z	ISB, ISB1
L	H	H	Output Disable	High-Z	Icc
L	H	L	Read	DOUT	Icc
L	L	X	Write	DIN	Icc

* X means Don't Care.

CMOS SRAM

Units:millimeters/Inches

Top View Dimensions:

- Overall Width: 23.90 MAX (0.941)
- Overall Height: 11.18 ± 0.12 (0.440 ± 0.005)
- Pin Pitch: 0.43 ± 0.10 (0.017 ± 0.002)
- Pin Width: 0.71 ± 0.10 (0.028 ± 0.004)
- Pin Spacing: 1.27 (0.050)
- Pin Height: 0.95 (0.0375)

Side View Dimensions:

- Overall Width: 9.40 ± 0.25 (0.370 ± 0.010)
- Overall Height: 10.16 (0.400)
- Pin Height: 0.69 MIN (0.027)
- Pin Spacing: 0.20 ± 0.10 (0.008 ± 0.002)

Bottom View Dimensions:

- Overall Width: 23.50 ± 0.12 (0.925 ± 0.005)
- Pin Pitch: 0.43 ± 0.10 (0.017 ± 0.002)
- Pin Width: 0.71 ± 0.10 (0.028 ± 0.004)
- Pin Spacing: 1.27 (0.050)
- Pin Height: 0.95 (0.0375)

Units:millimeters/Inches

